

a1  
Concl'd  
Moreover, it is necessary to adjust the substrate temperature in each step. In addition, it is undesirable from the point of view of thermal efficiency.

Page 8, delete the whole paragraph starting in line 18 and replace it with the following new paragraph:

a2  
Further, the inventors of the present invention have made examination in consideration of the aforementioned problem, resulting in a conception of the present invention configured as follows.

Page 8, delete the whole paragraph starting in line 22 and replace it with the following new paragraph:

a3  
That is, a method for producing a group III nitride compound semiconductor device, comprises:

Page 35, delete the whole paragraph starting in line 13 and replace it with the following new paragraph:

a4  
(1) A method for producing a group III nitride compound semiconductor device, comprising:

Page 36, delete the whole paragraph starting in line 22 and replace it with the following new paragraph:

a5  
A method for producing a group III nitride compound semiconductor device according to anyone of the above paragraphs after (1), wherein forming the undercoat layer is performed under the condition of a temperature in a range of from 1000°C to 1200°C.

Page 37, delete the whole paragraph starting in line 16 and replace it with the following new paragraph:

a6  
A method for producing a group III nitride compound semiconductor device according to any one of the above paragraphs after (1), further comprising forming a sedimentary layer before forming the undercoat layer.

Page 41, delete the whole paragraph starting in line 17 and replace it with the following new paragraph:

Q7

(6) A method for producing a laminate, comprising:

Page 42, delete the whole paragraph starting in line 2 and replace it with the following new paragraph:

Q8

(7) A method for producing a laminate, comprising:

Page 42, delete the whole paragraph starting in line 12 and replace it with the following new paragraph:

Q9

(8) A method for producing a laminate, comprising:

Page 42, delete the whole paragraph starting in line 22 and replace it with the following new paragraph:

Q10

A method for producing a laminate according to any one of the paragraphs (6) through (8), wherein forming the undercoat layer is performed under the condition of a temperature in a range of from 1000°C to 1200°C.

Page 43, delete the whole paragraph starting in line 13 and replace it with the following new paragraph:

Q11

A method for producing a laminate according to any one of the paragraphs (6) and thereafter, further comprising forming a sedimentary layer before forming the undercoat layer.

Page 43, delete the whole paragraph starting in line 17 and replace it with the following new paragraph:

Q12

(9) A method for producing a laminate, comprising:

Page 44, delete the whole paragraph starting in line 22 and replace it with the following new paragraph:

Q13

A method for producing a laminate according to any one of the paragraphs (9) and thereafter, wherein forming the undercoat layer is performed under the condition of a temperature in a range of from 1000°C to 1200°C.

Page 45, delete the whole paragraph starting in line 13 and replace it with the following new paragraph:

Q14 A method for producing a laminate according to any one of the paragraphs (9) and thereafter, further comprising forming a sedimentary layer before forming the undercoat layer.

Page 50, delete the whole paragraph starting in line 9 and replace it with the following new paragraph:

Q15 (17) A method for producing a group III nitride compound semiconductor device, comprising:

See the attached Appendix for the changes made to effect the above paragraph

IN THE CLAIMS:

Please cancel claims 8-31 without prejudice or disclaimer.

Please enter amended claims 1, 4 and 7 as follows:

Q16 Sub B1 1. (Amended) A group III nitride compound semiconductor device, comprising:  
a substrate;  
an undercoat layer formed on said substrate and having a surface with convex portions each shaped like a truncated hexagonal pyramid; and  
group III nitride compound semiconductor layers formed on said undercoat layer and having a device function.

Q17 Sub B3 4. (Amended) A group III nitride compound semiconductor device according to claim 2, wherein said undercoat layer is also doped with an n-type dopant and is of an n type as a whole.

Q18 Sub B5 7. (Amended) A group III nitride compound semiconductor device according to claim 1, wherein said group III nitride compound semiconductor layers have a function of one of a light-emitting device, a photodetector and an electronic device as a whole.

See the attached Appendix for the changes made to effect the above claim(s)

Please add claims 32 and 33 as follows:

Q19 Sub B6 32. (New) A group III nitride compound semiconductor device, comprising:  
a substrate;

an undercoat layer formed on said substrate and having a surface with a sectionally trapezoid shape; and

group III nitride semiconductor layers formed on said undercoat layer and having a device function.

33. (New) A group III nitride compound semiconductor device according to claim 32, wherein the sectionally trapezoid shape includes convex portions each shaped like a truncated hexagonal pyramid.

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